P-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	-20V
● I_D	-0.65A
● $R_{DS(ON)}$(at V_{GS}=-4.5V)	、 850 mohm
● $R_{DS(ON)}$(at V_{GS}=-2.5V)	、 1200 mohm
● $R_{DS(ON)}$(at V_{GS}=-1.8V)	、 2000

)Typical Performance Characteristics

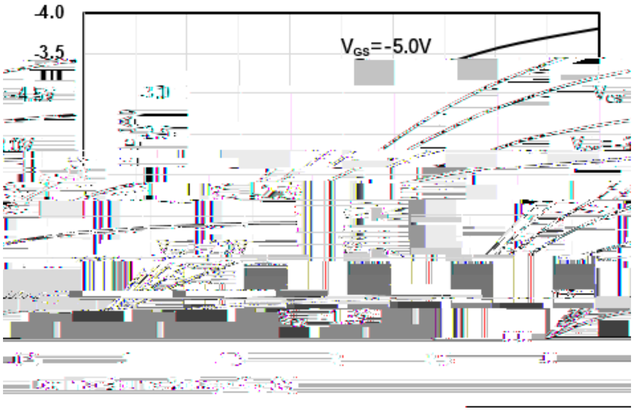


Figure1. Output Characteristics

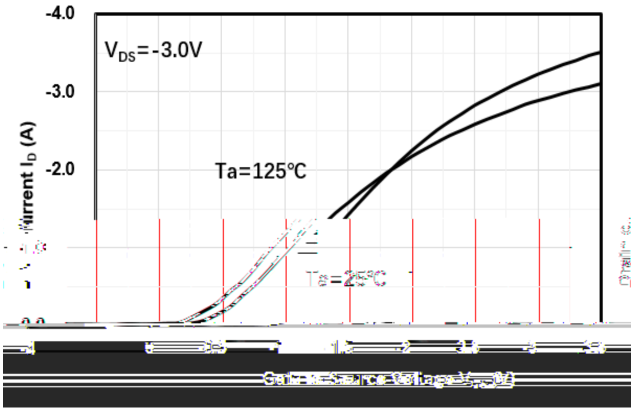


Figure2. Transfer Characteristics

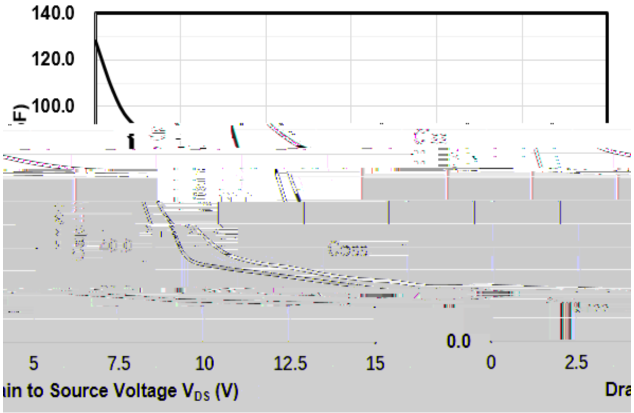


Figure3. Capacitance Characteristics

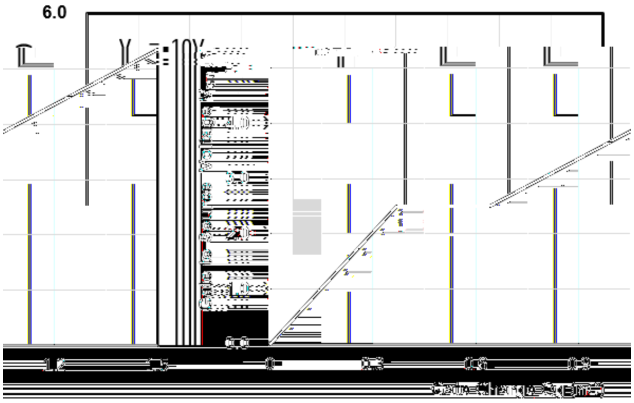


Figure4. Gate Charge

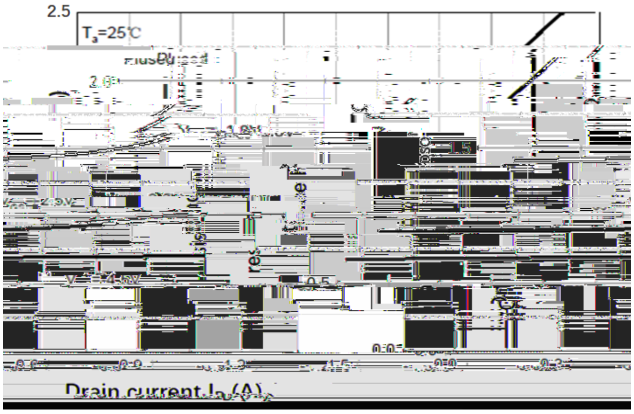


Figure5. Drain-Source on Resistance

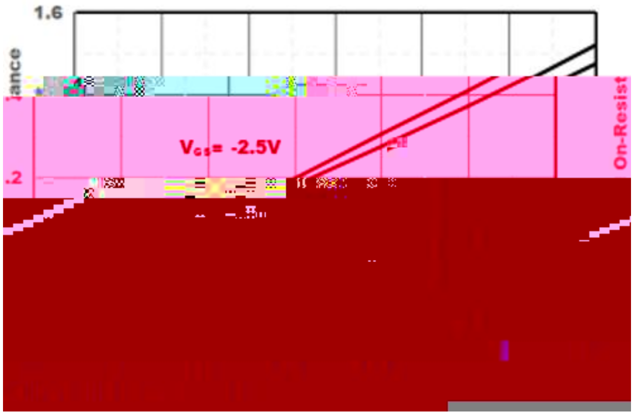


Figure6. Drain-Source on Resistance

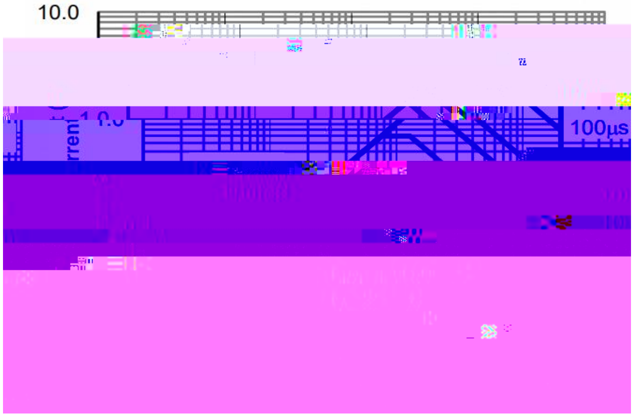


Figure7. Safe Operation Area

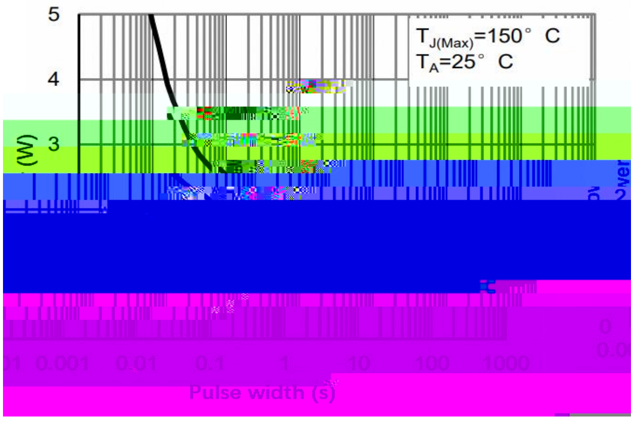


Figure8. Pulse Power Rating Junction-to Ambient

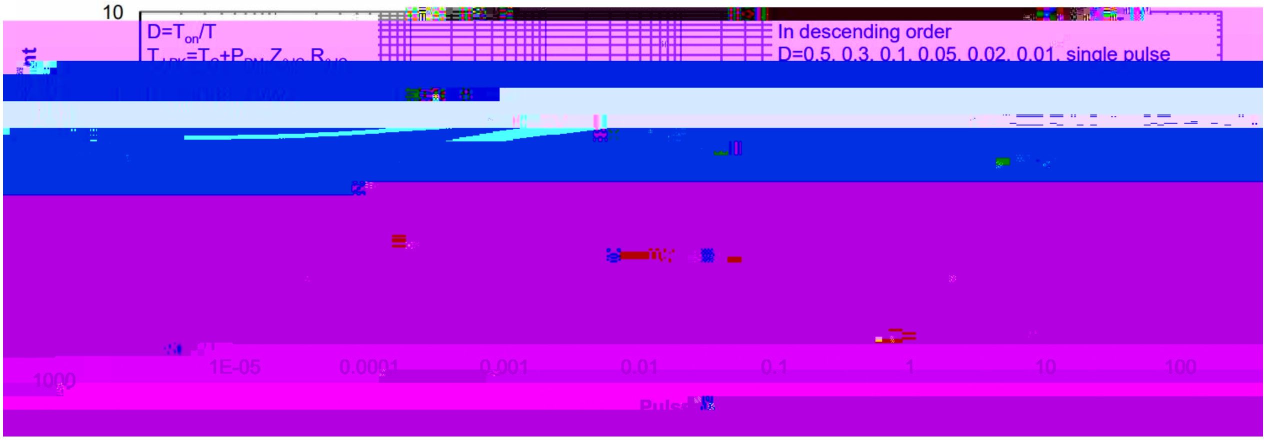
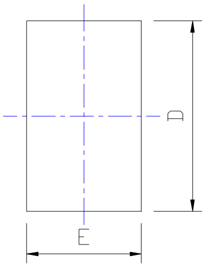
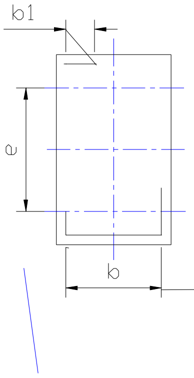


Figure9. Normalized Maximum Transient Thermal Impedance

■ DFN1006-3L Package information





UNIT' mm